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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/591,617	09/05/2006	Noboru Sakimura	20213	3312	
	7590 01/25/2008 TT MI IR PHV & PR FS		EXAMINER		
SCULLY SCOTT MURPHY & PRESSER, PC 400 GARDEN CITY PLAZA HUR, JUNG H				UNG H	
SUITE 300 GARDEN CIT	Y. NY 11530	·	ART UNIT PAPER NUMBER		
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			MAIL DATE	DELIVERY MODE	
			01/25/2008	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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	Application No.	Applicant(s)	• .
Office Aution 0	10/591,617	SAKIMURA ET AL.	
Office Action Summary	Examiner	Art Unit	
	Jung (John) H. Hur	2824	
The MAILING DATE of this communication a Period for Reply	appears on the cover sheet wit	h the correspondence add	ress
A SHORTENED STATUTORY PERIOD FOR REI WHICHEVER IS LONGER, FROM THE MAILING Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory per Failure to reply within the set or extended period for reply will, by sta Any reply received by the Office later than three months after the ma earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNIC 1.136(a). In no event, however, may a re tod will apply and will expire SIX (6) MONT tute. cause the application to become ABA	ATION. ply be timely filed THS from the mailing date of this con	
Status			
1) Responsive to communication(s) filed on	·.		
	his action is non-final.		
3) Since this application is in condition for allow	wance except for formal matte	ers, prosecution as to the	merits is
closed in accordance with the practice unde	er Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.	
Disposition of Claims			
4) ☐ Claim(s) 1-14 is/are pending in the application 4a) Of the above claim(s) is/are with definition 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1 and 2 is/are rejected. 7) ☐ Claim(s) 3-14 is/are objected to. 8) ☐ Claim(s) are subject to restriction and	rawn from consideration.		
Application Papers			
9) ☐ The specification is objected to by the Examination The drawing(s) filed on 28 November 2006 is Applicant may not request that any objection to the Replacement drawing sheet(s) including the corrupt The oath or declaration is objected to by the	s/are: a)⊠ accepted or b)□ he drawing(s) be held in abeyand ection is required if the drawing(s	ce. See 37 CFR 1.85(a). s) is objected to. See 37 CFF	R 1.121(d).
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for forei a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a li	ents have been received. ents have been received in Apriority documents have been reau (PCT Rule 17.2(a)).	pplication No received in this National S	itage
Attachment(s)	•		
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 10/23/06.		/Mail Date ormal Patent Application	

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DETAILED ACTION

1. Claims 1-14 are pending in the application.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 1 and 2 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Pat. Appl. Pub. No. 2004/0004856 ("SAKIMURA") in view of U.S. Pat. No. 6,545,906 ("SAVTCHENKO").

Regarding claim 1, SAKIMURA discloses a magnetoresistive random access memory (for example, Fig. 17) comprising: a plurality of first wirings (13) which is extended in a first direction (horizontal, in Fig. 17); a plurality of second wirings (74 and 76) which is extended in a second direction (vertical, in Fig. 17) which is substantially perpendicular to said first direction (see Fig. 17); a plurality of memory cells (72 and 75), each of which is placed correspondingly to each of positions where said plurality of first wirings is crossed with said plurality of second wirings (see Fig. 17); a second sense amplifier (85) which detects a state of a reference cell (for example, 75a) on the basis of an output from said reference cell (75a) provided by corresponding to a reference wiring (76) among said plurality of second wirings (74 and 76), among said plurality of memory cells (72 and 75); and a first sense amplifier (86) which detects a state of one (for example, 72a) of said plurality of memory cells (72 and 75) on the basis of an output

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(via 85) from said reference cell (75a) and an output (via 84) from said one (72a) of the plurality of memory cells, which is different from said reference cell (see Fig. 17), wherein each of said plurality of memory cells includes a magnetic tunneling junction element having a laminated free layer (i.e., a thin film of free layer; see Figs. 5A and 5B, as applied to Fig. 17) in which a magnetization direction is reversed correspondingly to data to be stored (see Figs. 5A and 5B).

SAKIMURA does not disclose that said magnetic tunneling junction element has a magnetization easy axis direction which is different from said first and second directions.

SAVTCHENKO discloses a magnetic tunneling junction element (for example, Figs. 1 and 2) having a magnetization easy axis direction (a diagonal direction of 53, 57 and 40 in Fig. 2) which is different from first and second directions (the direction of 20 and 30 in Fig. 2).

It would have been obvious at the time the invention was made to a person having ordinary skill in the art to use the magnetic tunneling junction elements of SAVTCHENKO in the memory of SAKIMURA, with appropriate changes to the peripheral circuit, for the purpose of enabling a new and improved means of writing to an MRAM device which is highly selectable, with an improved error rate and with a switching field that is less dependent on shape (see for example SAVTCHENKO column 2, lines 6-16).

Regarding claim 2, the above combination further discloses that a toggle operation (see for example Fig. 4 of SAVTCHENKO, as applied to the above combination) to reverse a magnetization of said laminated free layer, for a selected cell (for example, 72a in Fig. 17 of SAKIMURA, as applied to the above combination) as one of plurality of memory cells which corresponds to a selected first wiring selected among said plurality of first wirings and a selected

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second wiring selected among said plurality of second wirings, is executed by a series of current controls in which a first write current (IW 60, in Figs. 2 and 4 of SAVTCHENKO, as applied to the above combination) is supplied to said selected first wiring followed by a second write current (ID 70, in Figs. 2 and 4 of SAVTCHENKO, as applied to the above combination) to be supplied to said selected second wiring next, then, said first write current is stopped followed by said second write current to be stopped (see Fig. 4 of SAVTCHENKO, as applied to the above combination).

Allowable Subject Matter

4. Claims 3-14 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter:

Regarding claim 3, the prior arts of record do not disclose or suggest a magnetoresistive random access memory as recited in claim 3 *in toto* and particularly, in conjunction with other limitations, said first write current and said second write current are <u>larger</u> in said toggle operation executed <u>for said reference cell</u> than in said toggle operation executed for one of said plurality of memory cells which is different from said reference cell.

Regarding claim 4, the prior arts of record do not disclose or suggest a magnetoresistive random access memory as recited in claim 9 *in toto* and particularly, in conjunction with other limitations, a stored information of said <u>reference</u> cell is read out by executing a first read-out operation to detect a first state as an initial state of said reference cell, a first toggle operation to

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bring said reference cell into a second state by said toggle operation, a second read-out operation to detect said second state of said reference cell, <u>and</u> a second toggle operation to return said reference cell to said first state by said toggle operation, thereby stored information of the reference cell is read out on the basis of a comparison result between said first state and said second state. Claims 9-14 depend on claim 4.

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Regarding claim 5, the prior arts of record do not disclose or suggest a magnetoresistive random access memory as recited in claim 5 *in toto* and particularly, in conjunction with other limitations, a first toggle operation to bring said reference cell into a second state by said toggle operation, a <u>second</u> read-out operation to detect said second state of said reference cell, <u>and</u> a determination operation to determine said first state and said <u>second</u> state on the basis of a comparison result between said first state and said <u>second</u> state, thereby said second state is <u>retained</u> if said second state is equal to said stored information to be written to said reference cell, and said toggle operation is executed to <u>return</u> said reference cell to said first state if said second state is different from said stored information to be written to said reference cell, for writing.

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jung (John) H. Hur whose telephone number is (571) 272-1870. The examiner can normally be reached on M-F 8:00 AM - 4:30 PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard Elms can be reached on (571) 272-1869. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

ihh

/J. H. Hur/ Primary Patent Examiner Art Unit 2824 09 January 2008